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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Richard SPITZ et al.
Serial No. : 09/914,404
Filed : December 13, 2001
For : **METHOD FOR PRODUCING HEAVILY-DOPED
SEMICONDUCTOR COMPONENTS**
Group Art Unit : 2823
Examiner : Michelle Estrada

Commissioner for Patents
Washington, D.C. 20231

I hereby certify that this correspondence is being deposited with the
United States Postal Service as first class mail in an envelope
addressed to: Commissioner for Patents, Washington, D.C. 20231,
on

Date August 22, 2002

Signature

KENTON & KENTON

AMENDMENT

S I R:

In response to the Office Action mailed on May 22, 2002, please reconsider the
above-identified application based on the following:

IN THE CLAIMS:

Please amend without prejudice the claims as follows:

13. (Amended) A method for producing a semiconductor component in which at least
one doped region is introduced into a semiconductor wafer, comprising the steps of:
applying a solid glass layer provided with a dopant on at least one of two sides
of the semiconductor wafer;
heating the semiconductor wafer to a high temperature so that the dopant from
the solid glass layer penetrates into the semiconductor wafer to produce the at least
one doped region;
removing the solid glass layer; and
providing the dopant at a dosage of at least $10^{17}/\text{cm}^2$ in the at least one doped
region.